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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	18432
Number of I/O	80
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	132-WFQFN
Supplier Device Package	132-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a3p060-qng132

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC®3 device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges.

In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in [Figure 2-2 on page 2-5](#).

There are five regions to consider during power-up.

ProASIC3 I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points ([Figure 2-2 on page 2-5](#)).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:

Ramping up: $0.6\text{ V} < \text{trip_point_up} < 1.2\text{ V}$

Ramping down: $0.5\text{ V} < \text{trip_point_down} < 1.1\text{ V}$

VCC Trip Point:

Ramping up: $0.6\text{ V} < \text{trip_point_up} < 1.1\text{ V}$

Ramping down: $0.5\text{ V} < \text{trip_point_down} < 1\text{ V}$

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLLX exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see [Figure 2-2 on page 2-5](#) for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels ($0.75\text{ V} \pm 0.25\text{ V}$), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/Down Behavior of Low Power Flash Devices" chapter of the [ProASIC3 FPGA Fabric User's Guide](#) for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers

Output buffers, after 200 ns delay from input buffer activation.

Thermal Characteristics

Introduction

The temperature variable in the Microsemi Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ can be used to calculate junction temperature.

$$T_J = \text{Junction Temperature} = \Delta T + T_A$$

where:

T_A = Ambient Temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in [Table 2-5 on page 2-6](#).

P = Power dissipation

Table 2-15 • Different Components Contributing to the Static Power Consumption in ProASIC3 Devices

Parameter	Definition	Device Specific Static Power (mW)							
		A3P1000	A3P600	A3P400	A3P250	A3P125	A3P060	A3P030	A3P015
PDC1	Array static power in Active mode	See Table 2-7 on page 2-7.							
PDC2	I/O input pin static power (standard-dependent)	See Table 2-8 on page 2-7 through Table 2-10 on page 2-8.							
PDC3	I/O output pin static power (standard-dependent)	See Table 2-11 on page 2-9 through Table 2-13 on page 2-10.							
PDC4	Static PLL contribution	2.55 mW							
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-7 on page 2-7.							

Note: *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi Power spreadsheet calculator or SmartPower tool in Libero SoC software.

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-16 on page 2-14.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-17 on page 2-14.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-17 on page 2-14. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption— P_{TOTAL}

$$P_{TOTAL} = P_{STAT} + P_{DYN}$$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption— P_{STAT}

$$P_{STAT} = P_{DC1} + N_{INPUTS} * P_{DC2} + N_{OUTPUTS} * P_{DC3}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption— P_{DYN}

$$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$$

Global Clock Contribution— P_{CLOCK}

$$P_{CLOCK} = (P_{AC1} + N_{SPINE} * P_{AC2} + N_{ROW} * P_{AC3} + N_{S-CELL} * P_{AC4}) * F_{CLK}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide*.

Single-Ended I/O Characteristics

3.3 V LVTTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTTL input buffer and push-pull output buffer.

Table 2-37 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA ³	Max mA ³	μA ⁴	μA ⁴
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	–0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	–0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	10	10
24 mA	–0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-38 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA ³	Max mA ³	μA ⁴	μA ⁴
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	–0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	–0.3	0.8	2	3.6	0.4	2.4	16	16	109	103	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-51 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 μA	2 mA	Std.	0.60	15.86	0.04	1.54	0.43	15.86	13.51	4.09	3.80	19.25	16.90	ns
		–1	0.51	13.49	0.04	1.31	0.36	13.49	11.49	3.48	3.23	16.38	14.38	ns
		–2	0.45	11.84	0.03	1.15	0.32	11.84	10.09	3.05	2.84	14.38	12.62	ns
100 μA	4 mA	Std.	0.60	11.25	0.04	1.54	0.43	11.25	9.54	4.61	4.70	14.64	12.93	ns
		–1	0.51	9.57	0.04	1.31	0.36	9.57	8.11	3.92	4.00	12.46	11.00	ns
		–2	0.45	8.40	0.03	1.15	0.32	8.40	7.12	3.44	3.51	10.93	9.66	ns
100 μA	6 mA	Std.	0.60	11.25	0.04	1.54	0.43	11.25	9.54	4.61	4.70	14.64	12.93	ns
		–1	0.51	9.57	0.04	1.31	0.36	9.57	8.11	3.92	4.00	12.46	11.00	ns
		–2	0.45	8.40	0.03	1.15	0.32	8.40	7.12	3.44	3.51	10.93	9.66	ns
100 μA	8 mA	Std.	0.60	8.63	0.04	1.54	0.43	8.63	7.39	4.96	5.28	12.02	10.79	ns
		–1	0.51	7.34	0.04	1.31	0.36	7.34	6.29	4.22	4.49	10.23	9.18	ns
		–2	0.45	6.44	0.03	1.15	0.32	6.44	5.52	3.70	3.94	8.98	8.06	ns
100 μA	16 mA	Std.	0.60	8.05	0.04	1.54	0.43	8.05	6.93	5.03	5.43	11.44	10.32	ns
		–1	0.51	6.85	0.04	1.31	0.36	6.85	5.90	4.28	4.62	9.74	8.78	ns
		–2	0.45	6.01	0.03	1.15	0.32	6.01	5.18	3.76	4.06	8.55	7.71	ns
100 μA	24 mA	Std.	0.60	7.50	0.04	1.54	0.43	7.50	6.90	5.13	6.00	10.89	10.29	ns
		–1	0.51	6.38	0.04	1.31	0.36	6.38	5.87	4.36	5.11	9.27	8.76	ns
		–2	0.45	5.60	0.03	1.15	0.32	5.60	5.15	3.83	4.48	8.13	7.69	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-54 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
Applicable to Standard I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 μA	2 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		–1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		–2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 μA	4 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		–1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		–2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 μA	6 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		–1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		–2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns
100 μA	8 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		–1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		–2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. Software default selection highlighted in gray.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Timing Characteristics

Table 2-80 • 1.5 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.4\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	8.36	0.04	1.44	0.43	6.82	8.36	3.39	2.77	9.06	10.60	ns
	–1	0.56	7.11	0.04	1.22	0.36	5.80	7.11	2.88	2.35	7.71	9.02	ns
	–2	0.49	6.24	0.03	1.07	0.32	5.10	6.24	2.53	2.06	6.76	7.91	ns
4 mA	Std.	0.66	5.31	0.04	1.44	0.43	4.85	5.31	3.74	3.40	7.09	7.55	ns
	–1	0.56	4.52	0.04	1.22	0.36	4.13	4.52	3.18	2.89	6.03	6.42	ns
	–2	0.49	3.97	0.03	1.07	0.32	3.62	3.97	2.79	2.54	5.29	5.64	ns
6 mA	Std.	0.66	4.67	0.04	1.44	0.43	4.55	4.67	3.82	3.56	6.78	6.90	ns
	–1	0.56	3.97	0.04	1.22	0.36	3.87	3.97	3.25	3.03	5.77	5.87	ns
	–2	0.49	3.49	0.03	1.07	0.32	3.40	3.49	2.85	2.66	5.07	5.16	ns
8 mA	Std.	0.66	4.08	0.04	1.44	0.43	4.15	3.58	3.94	4.20	6.39	5.81	ns
	–1	0.56	3.47	0.04	1.22	0.36	3.53	3.04	3.36	3.58	5.44	4.95	ns
	–2	0.49	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns
12 mA	Std.	0.66	4.08	0.04	1.44	0.43	4.15	3.58	3.94	4.20	6.39	5.81	ns
	–1	0.56	3.47	0.04	1.22	0.36	3.53	3.04	3.36	3.58	5.44	4.95	ns
	–2	0.49	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

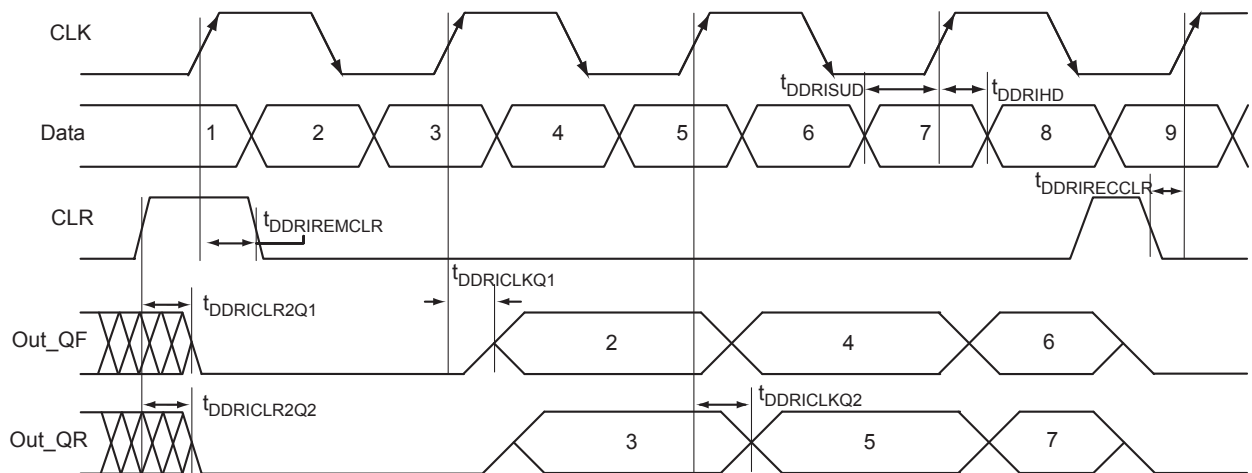


Figure 2-21 • Input DDR Timing Diagram

Timing Characteristics

Table 2-102 • Input DDR Propagation Delays

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{DDRICKQ1}	Clock-to-Out Out_QR for Input DDR	0.27	0.31	0.37	ns
t_{DDRICKQ2}	Clock-to-Out Out_QF for Input DDR	0.39	0.44	0.52	ns
t_{DDRISUD}	Data Setup for Input DDR (Fall)	0.25	0.28	0.33	ns
	Data Setup for Input DDR (Rise)	0.25	0.28	0.33	ns
t_{DDRILD}	Data Hold for Input DDR (Fall)	0.00	0.00	0.00	ns
	Data Hold for Input DDR (Rise)	0.00	0.00	0.00	ns
$t_{\text{DDRILR2Q1}}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.46	0.53	0.62	ns
$t_{\text{DDRILR2Q2}}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.57	0.65	0.76	ns
$t_{\text{DDRIREMCLR}}$	Asynchronous Clear Removal time for Input DDR	0.00	0.00	0.00	ns
$t_{\text{DDRIRECCLR}}$	Asynchronous Clear Recovery time for Input DDR	0.22	0.25	0.30	ns
$t_{\text{DDRILWCLR}}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.22	0.25	0.30	ns
$t_{\text{DDRICKMPWH}}$	Clock Minimum Pulse Width High for Input DDR	0.36	0.41	0.48	ns
$t_{\text{DDRICKMPWL}}$	Clock Minimum Pulse Width Low for Input DDR	0.32	0.37	0.43	ns
F_{DDRIMAX}	Maximum Frequency for Input DDR	350	309	263	MHz

Note: For specific junction temperature and voltage-supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

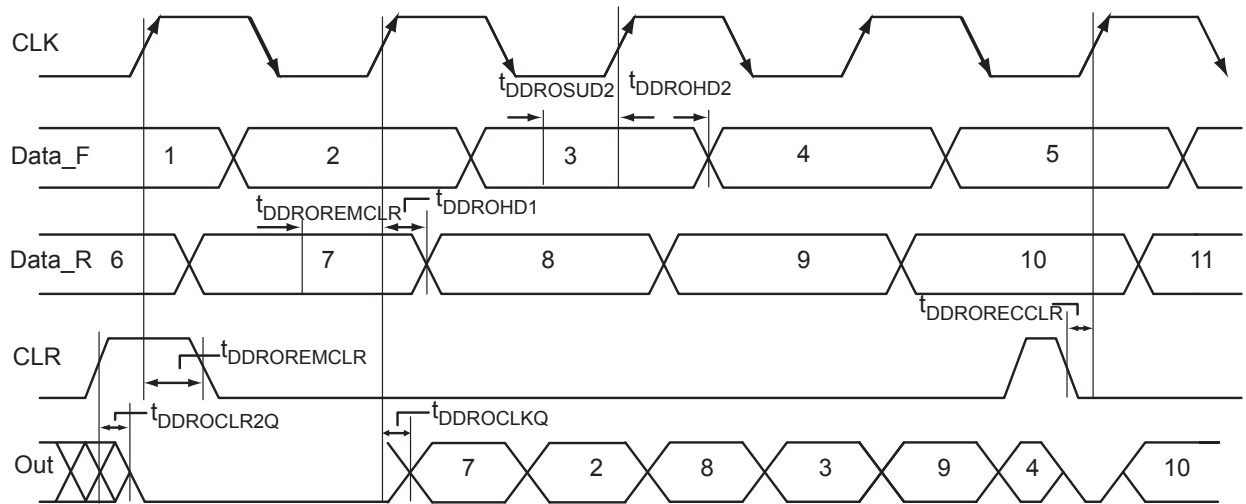


Figure 2-23 • Output DDR Timing Diagram

Timing Characteristics

Table 2-104 • Output DDR Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
$t_{DDROCLKQ}$	Clock-to-Out of DDR for Output DDR	0.70	0.80	0.94	ns
$t_{DDROSUD1}$	Data_F Data Setup for Output DDR	0.38	0.43	0.51	ns
$t_{DDROSUD2}$	Data_R Data Setup for Output DDR	0.38	0.43	0.51	ns
$t_{DDROHD1}$	Data_F Data Hold for Output DDR	0.00	0.00	0.00	ns
$t_{DDROHD2}$	Data_R Data Hold for Output DDR	0.00	0.00	0.00	ns
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out for Output DDR	0.80	0.91	1.07	ns
$t_{DDROEMCLR}$	Asynchronous Clear Removal Time for Output DDR	0.00	0.00	0.00	ns
$t_{DDROECCLR}$	Asynchronous Clear Recovery Time for Output DDR	0.22	0.25	0.30	ns
$t_{DDROWCLR1}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.22	0.25	0.30	ns
$t_{DDROCKMPWH}$	Clock Minimum Pulse Width High for the Output DDR	0.36	0.41	0.48	ns
$t_{DDROCKMPWL}$	Clock Minimum Pulse Width Low for the Output DDR	0.32	0.37	0.43	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	350	309	263	MHz

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The ProASIC3 library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the [Fusion](#), [IGLOO®/e](#), and [ProASIC3/E Macro Library Guide](#).

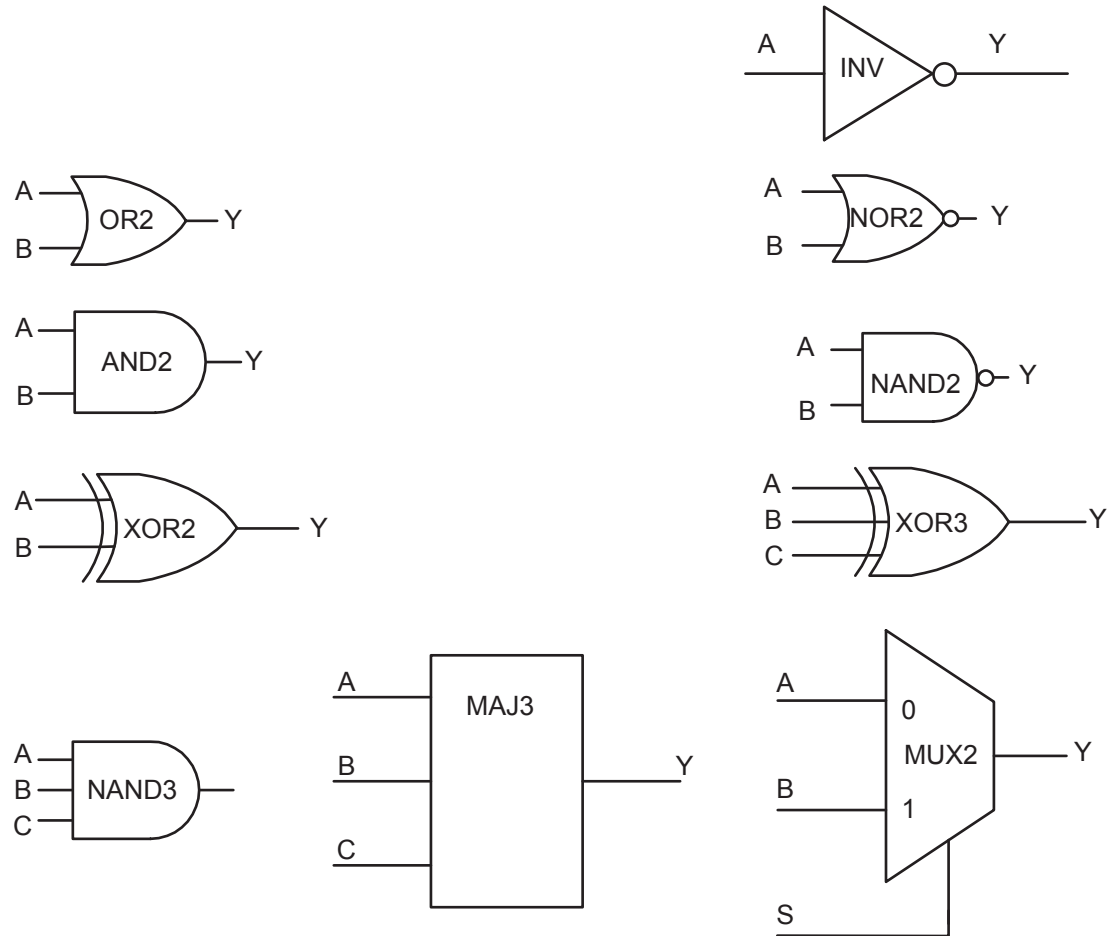


Figure 2-24 • Sample of Combinatorial Cells

Global Resource Characteristics

A3P250 Clock Tree Topology

Clock delays are device-specific. [Figure 2-28](#) is an example of a global tree used for clock routing. The global tree presented in [Figure 2-28](#) is driven by a CCC located on the west side of the A3P250 device. It is used to drive all D-flip-flops in the device.

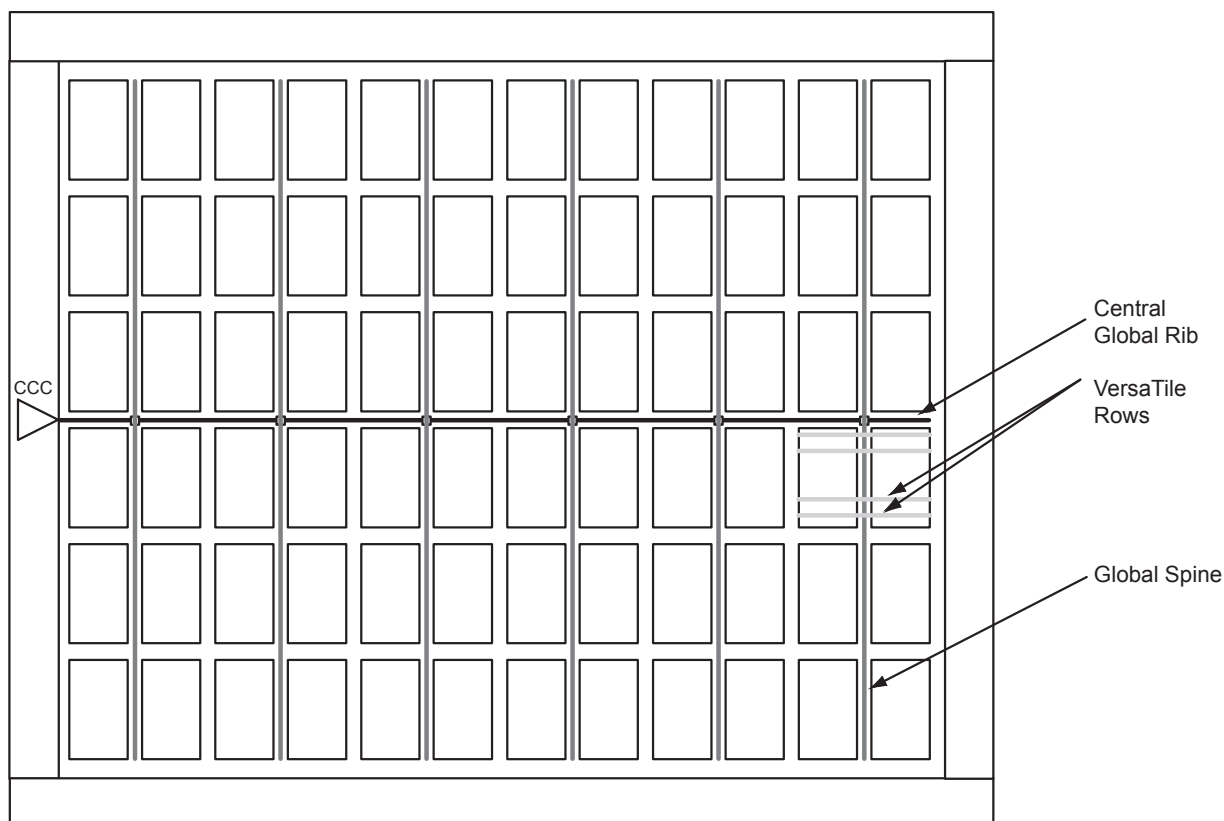


Figure 2-28 • Example of Global Tree Use in an A3P250 Device for Clock Routing

Global Tree Timing Characteristics

Global clock delays include the central rib delay, the spine delay, and the row delay. Delays do not include I/O input buffer clock delays, as these are I/O standard-dependent, and the clock may be driven and conditioned internally by the CCC module. For more details on clock conditioning capabilities, refer to the ["Clock Conditioning Circuits" section on page 2-90](#). [Table 2-108](#) to [Table 2-114 on page 2-89](#) present minimum and maximum global clock delays within each device. Minimum and maximum delays are measured with minimum and maximum loading.

Timing Waveforms

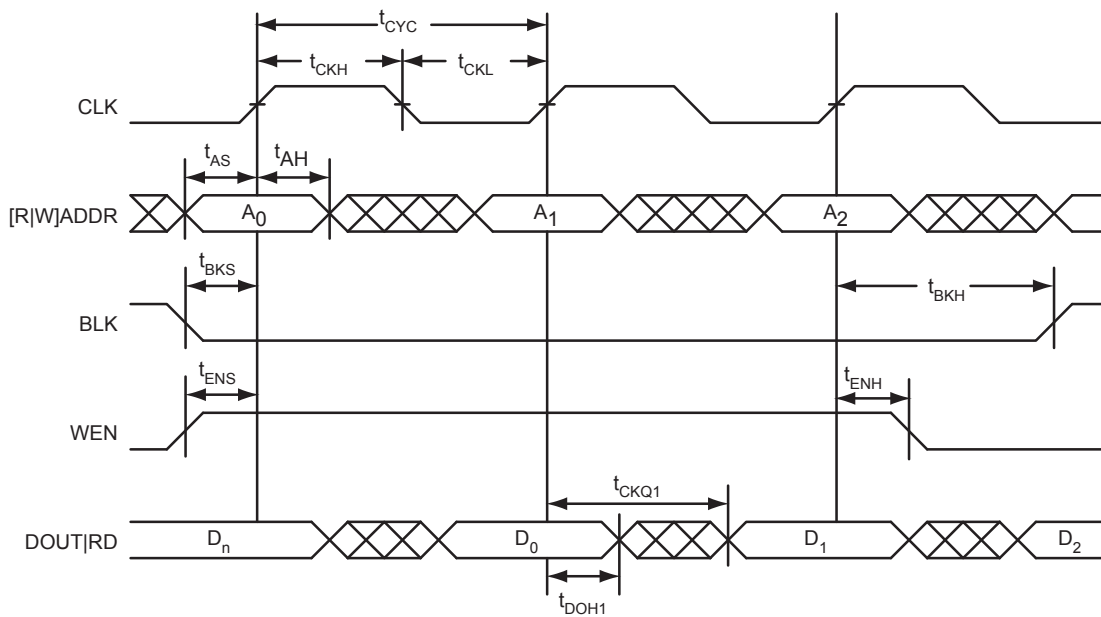


Figure 2-31 • RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.

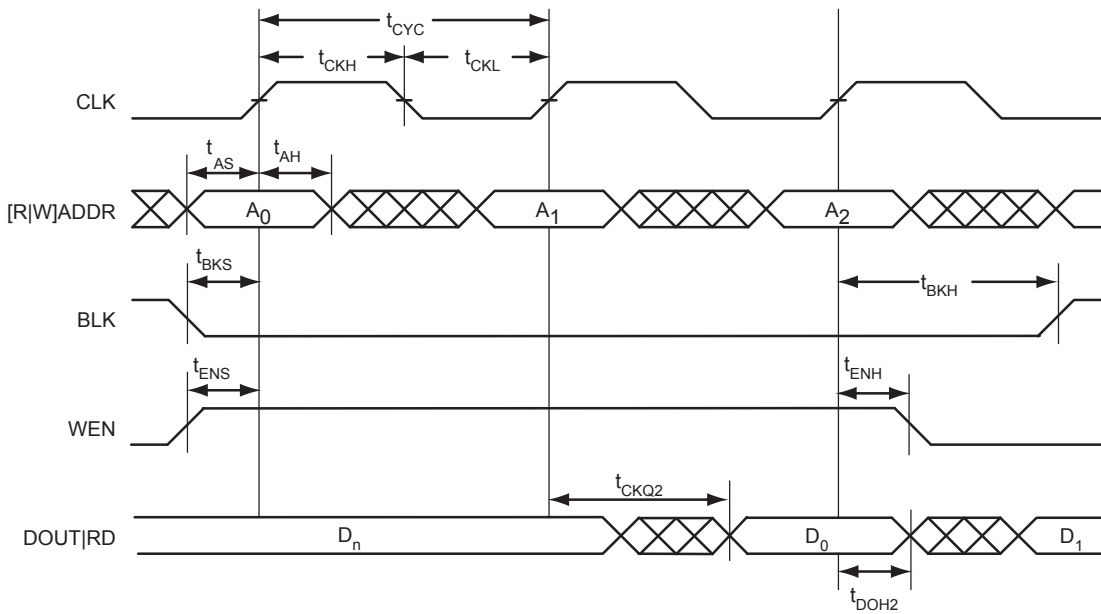


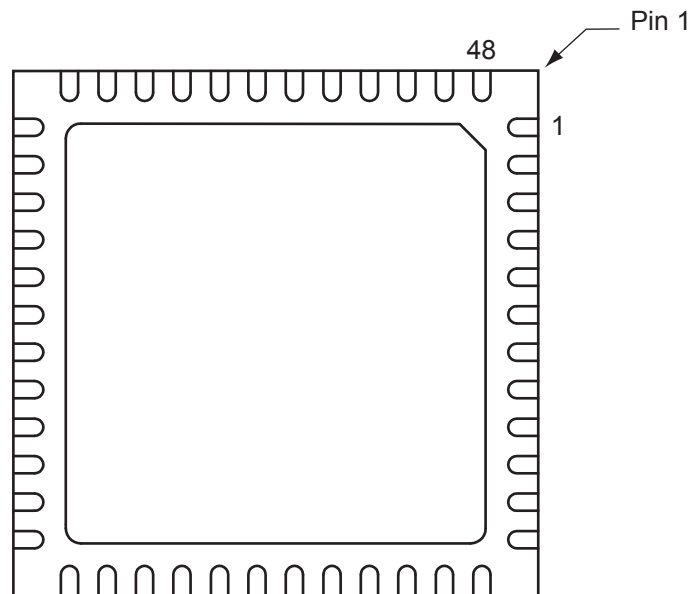
Figure 2-32 • RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.

Table 2-121 • A3P250 FIFO 1k×4**Worst Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$**

Parameter	Description	–2	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.05	4.61	5.42	ns
t_{ENH}	REN, WEN Hold Time	0.00	0.00	0.00	ns
t_{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t_{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t_{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
t_{REMRSTB}	RESET Removal	0.29	0.33	0.38	ns
t_{RECRSTB}	RESET Recovery	1.50	1.71	2.01	ns
t_{MPWRSTB}	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t_{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F_{MAX}	Maximum Frequency for FIFO	310	272	231	MHz

4 – Package Pin Assignments

QN48 – Bottom View



Note: The die attach paddle center of the package is tied to ground (GND).

Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

TQ144	
Pin Number	A3P060 Function
1	GAA2/IO51RSB1
2	IO52RSB1
3	GAB2/IO53RSB1
4	IO95RSB1
5	GAC2/IO94RSB1
6	IO93RSB1
7	IO92RSB1
8	IO91RSB1
9	VCC
10	GND
11	VCCIB1
12	IO90RSB1
13	GFC1/IO89RSB1
14	GFC0/IO88RSB1
15	GFB1/IO87RSB1
16	GFB0/IO86RSB1
17	VCOMPLF
18	GFA0/IO85RSB1
19	VCCPLF
20	GFA1/IO84RSB1
21	GFA2/IO83RSB1
22	GFB2/IO82RSB1
23	GFC2/IO81RSB1
24	IO80RSB1
25	IO79RSB1
26	IO78RSB1
27	GND
28	VCCIB1
29	GEC1/IO77RSB1
30	GEC0/IO76RSB1
31	GEB1/IO75RSB1
32	GEB0/IO74RSB1
33	GEA1/IO73RSB1
34	GEA0/IO72RSB1
35	VMV1
36	GNDQ

TQ144	
Pin Number	A3P060 Function
37	NC
38	GEA2/IO71RSB1
39	GEB2/IO70RSB1
40	GEC2/IO69RSB1
41	IO68RSB1
42	IO67RSB1
43	IO66RSB1
44	IO65RSB1
45	VCC
46	GND
47	VCCIB1
48	NC
49	IO64RSB1
50	NC
51	IO63RSB1
52	NC
53	IO62RSB1
54	NC
55	IO61RSB1
56	NC
57	NC
58	IO60RSB1
59	IO59RSB1
60	IO58RSB1
61	IO57RSB1
62	NC
63	GND
64	NC
65	GDC2/IO56RSB1
66	GDB2/IO55RSB1
67	GDA2/IO54RSB1
68	GNDQ
69	TCK
70	TDI
71	TMS
72	VMV1

TQ144	
Pin Number	A3P060 Function
73	VPUMP
74	NC
75	TDO
76	TRST
77	VJTAG
78	GDA0/IO50RSB0
79	GDB0/IO48RSB0
80	GDB1/IO47RSB0
81	VCCIB0
82	GND
83	IO44RSB0
84	GCC2/IO43RSB0
85	GCB2/IO42RSB0
86	GCA2/IO41RSB0
87	GCA0/IO40RSB0
88	GCA1/IO39RSB0
89	GCB0/IO38RSB0
90	GCB1/IO37RSB0
91	GCC0/IO36RSB0
92	GCC1/IO35RSB0
93	IO34RSB0
94	IO33RSB0
95	NC
96	NC
97	NC
98	VCCIB0
99	GND
100	VCC
101	IO30RSB0
102	GBC2/IO29RSB0
103	IO28RSB0
104	GBB2/IO27RSB0
105	IO26RSB0
106	GBA2/IO25RSB0
107	VMV0
108	GNDQ

PQ208	
Pin Number	A3P125 Function
109	TRST
110	VJTAG
111	GDA0/IO66RSB0
112	GDA1/IO65RSB0
113	GDB0/IO64RSB0
114	GDB1/IO63RSB0
115	GDC0/IO62RSB0
116	GDC1/IO61RSB0
117	NC
118	NC
119	NC
120	NC
121	NC
122	GND
123	VCCIB0
124	NC
125	NC
126	VCC
127	IO60RSB0
128	GCC2/IO59RSB0
129	GCB2/IO58RSB0
130	GND
131	GCA2/IO57RSB0
132	GCA0/IO56RSB0
133	GCA1/IO55RSB0
134	GCB0/IO54RSB0
135	GCB1/IO53RSB0
136	GCC0/IO52RSB0
137	GCC1/IO51RSB0
138	IO50RSB0
139	IO49RSB0
140	VCCIB0
141	GND
142	VCC
143	IO48RSB0
144	IO47RSB0

PQ208	
Pin Number	A3P125 Function
145	IO46RSB0
146	NC
147	NC
148	NC
149	GBC2/IO45RSB0
150	IO44RSB0
151	GBB2/IO43RSB0
152	IO42RSB0
153	GBA2/IO41RSB0
154	VMV0
155	GNDQ
156	GND
157	NC
158	GBA1/IO40RSB0
159	GBA0/IO39RSB0
160	GBB1/IO38RSB0
161	GBB0/IO37RSB0
162	GND
163	GBC1/IO36RSB0
164	GBC0/IO35RSB0
165	IO34RSB0
166	IO33RSB0
167	IO32RSB0
168	IO31RSB0
169	IO30RSB0
170	VCCIB0
171	VCC
172	IO29RSB0
173	IO28RSB0
174	IO27RSB0
175	IO26RSB0
176	IO25RSB0
177	IO24RSB0
178	GND
179	IO23RSB0
180	IO22RSB0

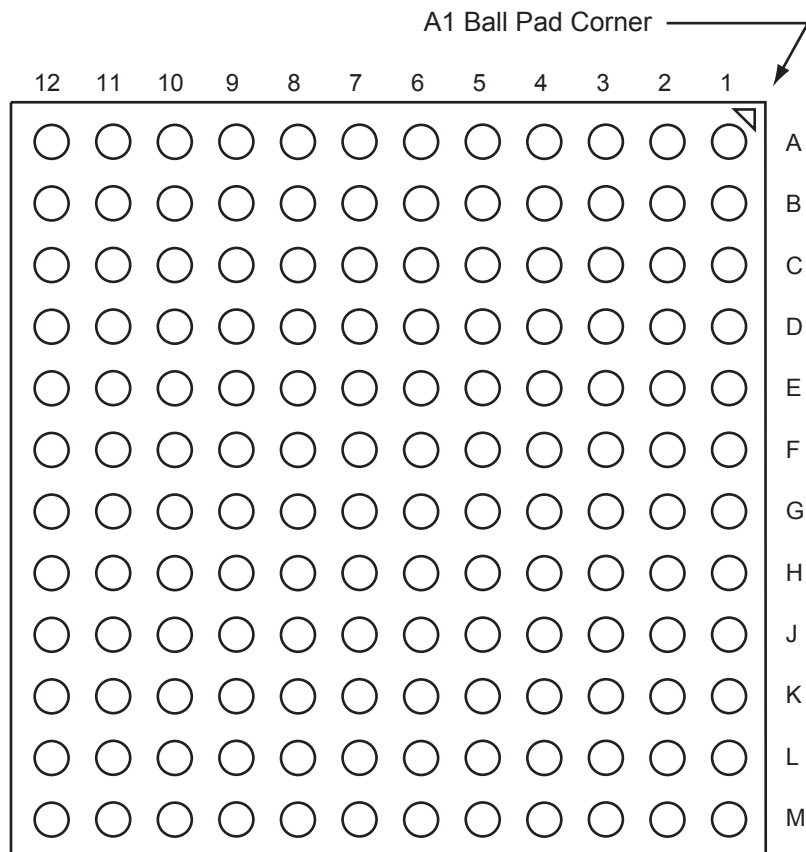
PQ208	
Pin Number	A3P125 Function
181	IO21RSB0
182	IO20RSB0
183	IO19RSB0
184	IO18RSB0
185	IO17RSB0
186	VCCIB0
187	VCC
188	IO16RSB0
189	IO15RSB0
190	IO14RSB0
191	IO13RSB0
192	IO12RSB0
193	IO11RSB0
194	IO10RSB0
195	GND
196	IO09RSB0
197	IO08RSB0
198	IO07RSB0
199	IO06RSB0
200	VCCIB0
201	GAC1/IO05RSB0
202	GAC0/IO04RSB0
203	GAB1/IO03RSB0
204	GAB0/IO02RSB0
205	GAA1/IO01RSB0
206	GAA0/IO00RSB0
207	GNDQ
208	VMV0

PQ208	
Pin Number	A3P250 Function
1	GND
2	GAA2/IO118UDB3
3	IO118VDB3
4	GAB2/IO117UDB3
5	IO117VDB3
6	GAC2/IO116UDB3
7	IO116VDB3
8	IO115UDB3
9	IO115VDB3
10	IO114UDB3
11	IO114VDB3
12	IO113PDB3
13	IO113NDB3
14	IO112PDB3
15	IO112NDB3
16	VCC
17	GND
18	VCCIB3
19	IO111PDB3
20	IO111NDB3
21	GFC1/IO110PDB3
22	GFC0/IO110NDB3
23	GFB1/IO109PDB3
24	GFB0/IO109NDB3
25	VCOMPLF
26	GFA0/IO108NPB3
27	VCCPLF
28	GFA1/IO108PPB3
29	GND
30	GFA2/IO107PDB3
31	IO107NDB3
32	GFB2/IO106PDB3
33	IO106NDB3
34	GFC2/IO105PDB3
35	IO105NDB3
36	NC

PQ208	
Pin Number	A3P250 Function
37	IO104PDB3
38	IO104NDB3
39	IO103PSB3
40	VCCIB3
41	GND
42	IO101PDB3
43	IO101NDB3
44	GEC1/IO100PDB3
45	GEC0/IO100NDB3
46	GEB1/IO99PDB3
47	GEB0/IO99NDB3
48	GEA1/IO98PDB3
49	GEA0/IO98NDB3
50	VMV3
51	GNDQ
52	GND
53	NC
54	NC
55	GEA2/IO97RSB2
56	GEB2/IO96RSB2
57	GEC2/IO95RSB2
58	IO94RSB2
59	IO93RSB2
60	IO92RSB2
61	IO91RSB2
62	VCCIB2
63	IO90RSB2
64	IO89RSB2
65	GND
66	IO88RSB2
67	IO87RSB2
68	IO86RSB2
69	IO85RSB2
70	IO84RSB2
71	VCC
72	VCCIB2

PQ208	
Pin Number	A3P250 Function
73	IO83RSB2
74	IO82RSB2
75	IO81RSB2
76	IO80RSB2
77	IO79RSB2
78	IO78RSB2
79	IO77RSB2
80	IO76RSB2
81	GND
82	IO75RSB2
83	IO74RSB2
84	IO73RSB2
85	IO72RSB2
86	IO71RSB2
87	IO70RSB2
88	VCC
89	VCCIB2
90	IO69RSB2
91	IO68RSB2
92	IO67RSB2
93	IO66RSB2
94	IO65RSB2
95	IO64RSB2
96	GDC2/IO63RSB2
97	GND
98	GDB2/IO62RSB2
99	GDA2/IO61RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	NC
108	TDO

FG144 – Bottom View



Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

FG256	
Pin Number	A3P400 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAA1/IO01RSB0
A4	GAB0/IO02RSB0
A5	IO16RSB0
A6	IO17RSB0
A7	IO22RSB0
A8	IO28RSB0
A9	IO34RSB0
A10	IO37RSB0
A11	IO41RSB0
A12	IO43RSB0
A13	GBB1/IO57RSB0
A14	GBA0/IO58RSB0
A15	GBA1/IO59RSB0
A16	GND
B1	GAB2/IO154UDB3
B2	GAA2/IO155UDB3
B3	IO12RSB0
B4	GAB1/IO03RSB0
B5	IO13RSB0
B6	IO14RSB0
B7	IO21RSB0
B8	IO27RSB0
B9	IO32RSB0
B10	IO38RSB0
B11	IO42RSB0
B12	GBC1/IO55RSB0
B13	GBB0/IO56RSB0
B14	IO44RSB0
B15	GBA2/IO60PDB1
B16	IO60NDB1
C1	IO154VDB3
C2	IO155VDB3
C3	IO11RSB0
C4	IO07RSB0

FG256	
Pin Number	A3P400 Function
C5	GAC0/IO04RSB0
C6	GAC1/IO05RSB0
C7	IO20RSB0
C8	IO24RSB0
C9	IO33RSB0
C10	IO39RSB0
C11	IO45RSB0
C12	GBC0/IO54RSB0
C13	IO48RSB0
C14	VMV0
C15	IO61NPB1
C16	IO63PDB1
D1	IO151VDB3
D2	IO151UDB3
D3	GAC2/IO153UDB3
D4	IO06RSB0
D5	GNDQ
D6	IO10RSB0
D7	IO19RSB0
D8	IO26RSB0
D9	IO30RSB0
D10	IO40RSB0
D11	IO46RSB0
D12	GNDQ
D13	IO47RSB0
D14	GBB2/IO61PPB1
D15	IO53RSB0
D16	IO63NDB1
E1	IO150PDB3
E2	IO08RSB0
E3	IO153VDB3
E4	IO152VDB3
E5	VMV0
E6	VCCIB0
E7	VCCIB0
E8	IO25RSB0

FG256	
Pin Number	A3P400 Function
E9	IO31RSB0
E10	VCCIB0
E11	VCCIB0
E12	VMV1
E13	GBC2/IO62PDB1
E14	IO65RSB1
E15	IO52RSB0
E16	IO66PDB1
F1	IO150NDB3
F2	IO149NPB3
F3	IO09RSB0
F4	IO152UDB3
F5	VCCIB3
F6	GND
F7	VCC
F8	VCC
F9	VCC
F10	VCC
F11	GND
F12	VCCIB1
F13	IO62NDB1
F14	IO49RSB0
F15	IO64PPB1
F16	IO66NDB1
G1	IO148NDB3
G2	IO148PDB3
G3	IO149PPB3
G4	GFC1/IO147PPB3
G5	VCCIB3
G6	VCC
G7	GND
G8	GND
G9	GND
G10	GND
G11	VCC
G12	VCCIB1

FG256	
Pin Number	A3P1000 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAA1/IO01RSB0
A4	GAB0/IO02RSB0
A5	IO16RSB0
A6	IO22RSB0
A7	IO28RSB0
A8	IO35RSB0
A9	IO45RSB0
A10	IO50RSB0
A11	IO55RSB0
A12	IO61RSB0
A13	GBB1/IO75RSB0
A14	GBA0/IO76RSB0
A15	GBA1/IO77RSB0
A16	GND
B1	GAB2/IO224PDB3
B2	GAA2/IO225PDB3
B3	GNDQ
B4	GAB1/IO03RSB0
B5	IO17RSB0
B6	IO21RSB0
B7	IO27RSB0
B8	IO34RSB0
B9	IO44RSB0
B10	IO51RSB0
B11	IO57RSB0
B12	GBC1/IO73RSB0
B13	GBB0/IO74RSB0
B14	IO71RSB0
B15	GBA2/IO78PDB1
B16	IO81PDB1
C1	IO224NDB3
C2	IO225NDB3
C3	VMV3
C4	IO11RSB0
C5	GAC0/IO04RSB0
C6	GAC1/IO05RSB0

FG256	
Pin Number	A3P1000 Function
C7	IO25RSB0
C8	IO36RSB0
C9	IO42RSB0
C10	IO49RSB0
C11	IO56RSB0
C12	GBC0/IO72RSB0
C13	IO62RSB0
C14	VMV0
C15	IO78NDB1
C16	IO81NDB1
D1	IO222NDB3
D2	IO222PDB3
D3	GAC2/IO223PDB3
D4	IO223NDB3
D5	GNDQ
D6	IO23RSB0
D7	IO29RSB0
D8	IO33RSB0
D9	IO46RSB0
D10	IO52RSB0
D11	IO60RSB0
D12	GNDQ
D13	IO80NDB1
D14	GBB2/IO79PDB1
D15	IO79NDB1
D16	IO82NSB1
E1	IO217PDB3
E2	IO218PDB3
E3	IO221NDB3
E4	IO221PDB3
E5	VMV0
E6	VCCIB0
E7	VCCIB0
E8	IO38RSB0
E9	IO47RSB0
E10	VCCIB0
E11	VCCIB0
E12	VMV1

FG256	
Pin Number	A3P1000 Function
E13	GBC2/IO80PDB1
E14	IO83PPB1
E15	IO86PPB1
E16	IO87PDB1
F1	IO217NDB3
F2	IO218NDB3
F3	IO216PDB3
F4	IO216NDB3
F5	VCCIB3
F6	GND
F7	VCC
F8	VCC
F9	VCC
F10	VCC
F11	GND
F12	VCCIB1
F13	IO83NPB1
F14	IO86NPB1
F15	IO90PPB1
F16	IO87NDB1
G1	IO210PSB3
G2	IO213NDB3
G3	IO213PDB3
G4	GFC1/IO209PPB3
G5	VCCIB3
G6	VCC
G7	GND
G8	GND
G9	GND
G10	GND
G11	VCC
G12	VCCIB1
G13	GCC1/IO91PPB1
G14	IO90NPB1
G15	IO88PDB1
G16	IO88NDB1
H1	GFB0/IO208NPB3
H2	GFA0/IO207NDB3

Revision	Changes	Page
Revision 9 (Oct 2009) Product Brief v1.3	The CS121 package was added to table under "Features and Benefits" section, the "I/Os Per Package 1" table, Table 1 • ProASIC3 FPGAs Package Sizes Dimensions, "ProASIC3 Ordering Information", and the "Temperature Grade Offerings" table.	I – IV
	"ProASIC3 Ordering Information" was revised to include the fact that some RoHS compliant packages are halogen-free.	IV
	Packaging v1.5 The "CS121 – Bottom View" figure and pin table for A3P060 are new.	4-15
Revision 8 (Aug 2009) Product Brief v1.2 DC and Switching Characteristics v1.4	All references to M7 devices (CoreMP7) and speed grade –F were removed from this document.	N/A
	Table 1-1 I/O Standards supported is new.	1-7
	The I/Os with Advanced I/O Standards section was revised to add definitions of hot-swap and cold-sparing.	1-7
	3.3 V LVCMOS and 1.2 V LVCMOS Wide Range support was added to the datasheet. This affects all tables that contained 3.3 V LVCMOS and 1.2 V LVCMOS data.	N/A
	I_{IL} and I_{IH} input leakage current information was added to all "Minimum and Maximum DC Input and Output Levels" tables.	N/A
	–F was removed from the datasheet. The speed grade is no longer supported.	N/A
	The notes in Table 2-2 • Recommended Operating Conditions 1 were updated.	2-2
	Table 2-4 • Overshoot and Undershoot Limits 1 was updated.	2-3
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays was updated.	2-6
	In Table 2-116 • RAM4K9, the following specifications were removed: t_{WRO} t_{CCKH}	2-96
	In Table 2-117 • RAM512X18, the following specifications were removed: t_{WRO} t_{CCKH}	2-97
	In the title of Table 2-74 • 1.8 V LVCMOS High Slew, VCCI had a typo. It was changed from 3.0 V to 1.7 V.	2-58
Revision 7 (Feb 2009) Product Brief v1.1	The "Advanced I/O" section was revised to add a bullet regarding wide range power supply voltage support.	I
	The table under "Features and Benefits" section, was updated to include a value for typical equivalent macrocells for A3P250.	I
	The QN48 package was added to the following tables: the table under "Features and Benefits" section, "I/Os Per Package 1" "ProASIC3 FPGAs Package Sizes Dimensions", and "Temperature Grade Offerings". The number of singled-ended I/Os for QN68 was added to the "I/Os Per Package 1" table.	N/A
	The Wide Range I/O Support section is new.	1-7
Revision 6 (Dec 2008) Packaging v1.4	The "QN48 – Bottom View" section is new.	4-1
	The "QN68" pin table for A3P030 is new.	4-5